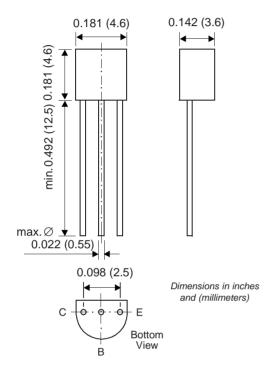


Vishay Semiconductors formerly General Semiconductor

Small Signal Transistors (NPN)



TO-226AA (TO-92)



Features

- NPN Silicon Epitaxial Planar Transistors for switching and amplifier applications. Especially suited for AF-driver stages and low power output stages.
- These types are also available subdivided into three groups -16, -25, and -40, according to their DC current gain. As complementary types, the PNP transistors BC327 and BC328 are recommended.
- On special request, this transistor is also manufactured in the pin configuration TO-18.

Mechanical Data

Case: TO-92 Plastic Package

Weight: approx. 0.18g

Packaging Codes/Options:

E6/Bulk – 5K per container, 20K/box E7/4K per Ammo mag., 20K/box

Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

	•	-	•
	Symbol	Value	Unit
BC337 BC338	VCES	50 30	V
BC337 BC338	VCEO	45 25	V
	VEBO	5	V
	Ic	800	mA
	I _{CM}	1	А
	IB	100	mA
	Ptot	625 ⁽¹⁾	mW
ient Air	R _θ JA	200 ⁽¹⁾	°C/W
	Tj	150	°C
	Ts	-65 to +150	°C
	BC338 BC337	BC337 BC338 VCES BC337 BC338 VEBO IC ICM IB Ptot ient Air ReJA Tj	BC337 BC338 VCES 50 30 BC337 VCEO 45 25 VEBO 5 IC 800 ICM 1 IB 100 Ptot 625 ⁽¹⁾ ilent Air ReJA 200 ⁽¹⁾ Tj 150

Note:

(1) Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

BC337 and BC338

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Electrical Characteristics (T_J = 25°C unless otherwise noted)

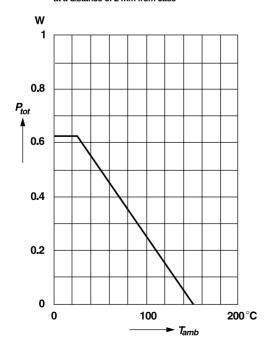
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Current gain group -16 -25 -40	hFE	VcE = 1 V, Ic = 100 mA	100 160 250	160 250 400	250 400 630	
DC Current Gain Current gain group -16 -25 -40		V _{CE} = 1 V, I _C = 300 mA	60 100 170	130 200 320	_ _ _	_
Collector-Emitter Cutoff Current BC337 BC338 BC337 BC338	Ices	VCE = 45 V VCE = 25 V VCE = 45 V, T _{amb} = 125°C VCE = 25 V, T _{amb} = 125°C	_ _ _ _	2 2 —	100 100 10 10	nA nA μA μA
Collector-Emitter Breakdown Voltage BC337 BC338	V(BR)CEO	Ic = 10 mA	45 20	_	_	V
Collector-Emitter Breakdown Voltage BC337 BC338	V(BR)CES	Ic = 0.1 mA	50 30	_	_	V
Emitter-Base Breakdown Voltage	V(BR)EBO	IE = 0.1 mA	5	_	_	V
Collector Saturation Voltage	VCEsat	Ic = 500 mA, I _B = 50 mA	_	_	0.7	V
Base-Emitter Voltage	VBE	V _{CE} = 1 V, I _C = 300 mA	_	_	1.2	V
Gain-Bandwidth Product	fτ	VcE = 5 V, Ic = 10 mA f = 50 MHz	_	100	_	MHz
Collector-Base Capacitance	Ссво	VcB = 10 V, f = 1 MHz	_	12		pF

Ratings and

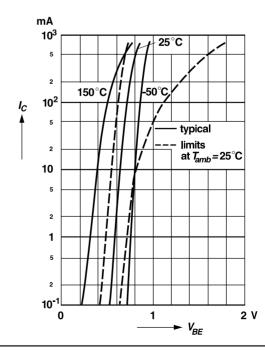
Characteristic Curves (TA = 25°C unless otherwise noted)

Admissible power dissipation versus ambient temperature

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



Collector current versus base-emitter voltage



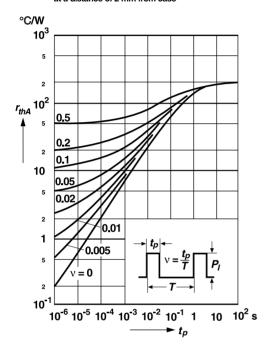


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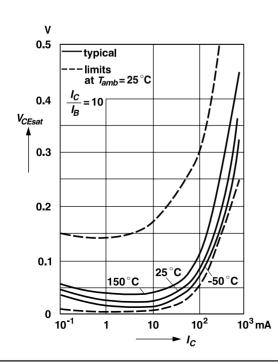
Ratings and Characteristic Curves (TA = 25°C unless otherwise noted)

Pulse thermal resistance versus pulse duration

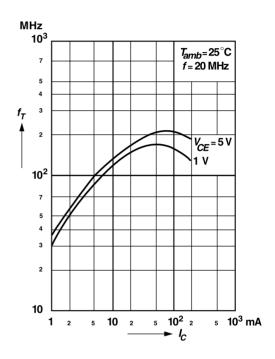
Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



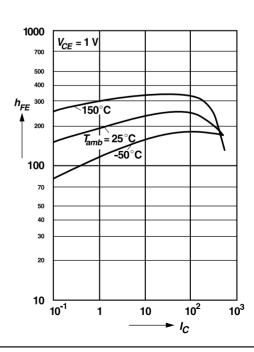
Collector saturation voltage versus collector current



Gain-bandwidth product versus collector current



DC current gain versus collector current



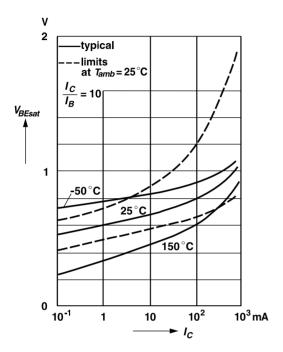
BC337 and BC338

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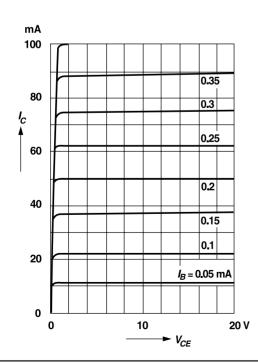
VISHAY

Ratings and Characteristic Curves (TA = 25°C unless otherwise noted)

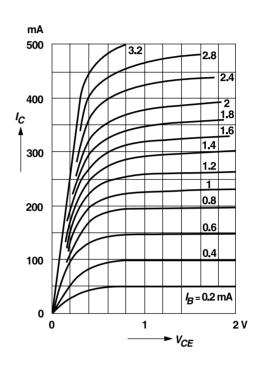
Base saturation voltage versus collector current



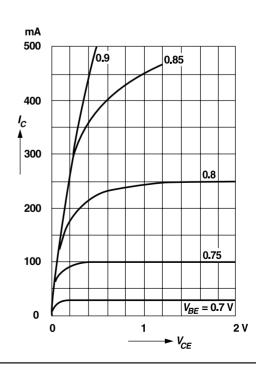
Common emitter collector characteristics



Common emitter collector characteristics



Common emitter collector characteristics



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